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Inclosure Material:	
Metal all transistor	
Overall Length:	
1.573 inches all transistor	
Overall Height:	
0.350 inches all transistor	
Overall Width:	
1.050 inches all transistor	
Mounting Facility Quantity:	
2 all transistor	
Internal Configuration:	
Junction contact all transistor	
Joint Electronic Device Engineering Co	uncil/jedec/case Outline Designation:
To-3 all transistor	
Electrode Internally-electrically Connec	ted To Case:
Collector all transistor	
Internal Junction Configuration:	
Pnp all transistor	
Component Function Relationship:	
Matched	
Component Name And Quantity:	
2 transistor	
Mounting Method:	
Unthreaded hole all transistor	
Semiconductor Material:	
Germanium all transistor	
Voltage Rating In Volts Per Characterist	iic:
50.0 breakdown voltage, collector-to-emit	tter, base open all transistor and 75.0 breakdown voltage, collector-to-base, emitter open al
transistor and 5.0 breakdown voltage, em	itter-to-base, collector open all transistor
Current Rating Per Characteristic:	
11.00 amperes source cutoff current all tra	ansistor
Power Rating Per Characteristic:	
40.0 watts small-signal input power, comn	non-collector preset all transistor
Maximum Operating Tempurature Per M	leasurement Point:
110.0 degrees celsius junction all transisto	r
Terminal Type And Quantity:	
2 pin all transistor and 1 case all transistor	
Shelf Life:	
N/a	
Unit Of Measure:	
-	
Demilitarization:	

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